

SOT-23 Formed SMD Package

**CMBTA42
CMBTA43**

SILICON EPITAXIAL TRANSISTORS

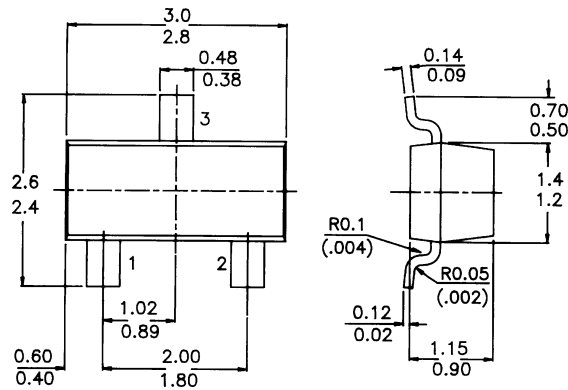
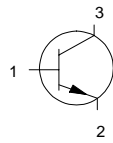
N-P-N transistors

Marking

CMBTA42 = 1D
CMBTA43 = 1E

**PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm**

Pin configuration
1 = BASE
2 = EMITTER
3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

	CMBTA42	A43
Collector-base voltage (open emitter)	V_{CBO} max. 300	200 V
Collector-emitter voltage (open base)	V_{CEO} max. 300	200 V
Emitter-base voltage (open collector)	V_{EBO} max. 6	V
Collector current (d.c.)	I_C max. 500	mA
Total power dissipation up to $T_{amb} = 25\text{ }^\circ\text{C}$	P_{tot} max. 250	mW
Junction temperature	T_j max. 150	$^\circ\text{C}$
D.C. current gain	h_{FE} min. 40	
Transition frequency at $f = 35\text{ MHz}$	f_T min. 50	MHz
Feedback capacitance at $f = 1\text{ MHz}$	C_{re} max. 3	4 pF

CMBTA42
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RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CBO}	max. 300	200	V
Collector-emitter voltage (open base)	V_{CEO}	max. 300	200	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6	V
Collector current (d.c.)	I_C	max.	500	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250	mW
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.	150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$$T_j = P (R_{th\ j-t} + R_{th\ t-s} + R_{th\ s-a}) + T_{amb}$$

Thermal resistance

from junction to ambient $R_{th\ j-a} = 500$ K/W

CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

		CMBTA42	A43	
Collector-emitter breakdown voltage		min. 300	200	V
$I_C = 1$ mA; $I_B = 0$	$V_{(BR)CEO}$			
Collector-base breakdown voltage		min. 300	200	V
$I_C = 100$ μA ; $I_E = 0$	$V_{(BR)CBO}$			
Emitter-base breakdown voltage		min.	6	V
$I_E = 100$ μA ; $I_C = 0$	$V_{(BR)EBO}$			
Collector cut-off current		I_{CBO}	max. 0.1	- μA
$I_E = 0$; $V_{CB} = 200$ V		I_{CBO}	max. -	0.1 μA
$I_E = 0$; $V_{CB} = 160$ V		I_{EBO}	max. 0.1	- μA
Emitter cut-off current		I_{EBO}	max. -	0.1 μA
$I_C = 0$; $V_{BE} = 6$ V		C_{re}	max. 3	4 pF
$I_C = 0$; $V_{BE} = 4$ V				
Feedback capacitance at $f = 1$ MHz				
$I_E = 0$; $V_{CB} = 20$ V				
Saturation voltages		V_{CEsat}	max. 0.5	V
$I_C = 20$ mA; $I_B = 2$ mA		V_{BEsat}	max. 0.9	V
$I_C = 20$ mA; $I_B = 2$ mA		h_{FE}	min. 25	
D.C. current gain		h_{FE}	min. 40	
$I_C = 1$ mA; $V_{CE} = 10$ V		h_{FE}	min. 40	
$I_C = 10$ mA; $V_{CE} = 10$ V				
$I_C = 30$ mA; $V_{CE} = 10$ V		f_T	min. 50	MHz
Transition frequency at $f = 35$ MHz				
$I_C = 10$ mA; $V_{CE} = 20$ V				

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